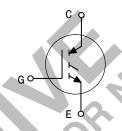
## Designer's™ Data Sheet

# **Insulated Gate Bipolar Transistor**

## N-Channel Enhancement-Mode Silicon Gate

This Insulated Gate Bipolar Transistor (IGBT) uses an advanced termination scheme to provide an enhanced and reliable high voltage—blocking capability. Short circuit rated IGBT's are specifically suited for applications requiring a guaranteed short circuit withstand time. Fast switching characteristics result in efficient operation at high frequencies.

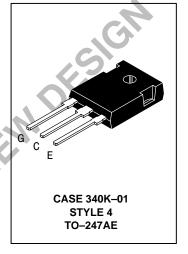
- Industry Standard High Power TO–247 Package with Isolated Mounting Hole
- High Speed E<sub>off</sub>: 160 μJ/A typical at 125°C
- High Short Circuit Capability 10 μs minimum
- Robust High Voltage Termination



## **MGW20N120**

Motorola Preferred Device

IGBT IN TO-247
20 A @ 90°C
28 A @ 25°C
1200 VOLTS
SHORT CIRCUIT RATED



#### MAXIMUM RATINGS (T<sub>.1</sub> = 25°C unless otherwise noted)

| Rating  | Symbol  | Value          | Unit          |
|---|---|----------------|---------------|
| Collector–Emitter Voltage   | V <sub>CES</sub>  | 1200           | Vdc           |
| Collector–Gate Voltage ( $R_{GE} = 1.0 \text{ M}\Omega$ )   | V <sub>CGR</sub>  | 1200           | Vdc           |
| Gate-Emitter Voltage — Continuous   | $V_{GE}$  | ±20            | Vdc           |
| Collector Current — Continuous @ T <sub>C</sub> = 25°C<br>— Continuous @ T <sub>C</sub> = 90°C<br>— Repetitive Pulsed Current (1) | I <sub>C25</sub><br>I <sub>C90</sub><br>I <sub>CM</sub> | 28<br>20<br>56 | Adc<br>Apk    |
| Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C   | P <sub>D</sub>  | 174<br>1.39    | Watts<br>W/°C |
| Operating and Storage Junction Temperature Range  | T <sub>J</sub> , T <sub>stg</sub>                       | -55 to 150     | °C            |
| Short Circuit Withstand Time $(V_{CC}=720\ Vdc,\ V_{GE}=15\ Vdc,\ T_J=125^{\circ}C,\ R_G=20\ \Omega)$                             | t <sub>sc</sub>   | 10             | μS            |
| Thermal Resistance — Junction to Case – IGBT — Junction to Ambient  | R <sub>θJC</sub><br>R <sub>θJA</sub>                    | 0.7<br>35      | °C/W          |
| Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds   | TL  | 260            | °C            |
| Mounting Torque, 6–32 or M3 screw   | 10 lbf•in (1.13 N•m)                                    |                |               |

<sup>(1)</sup> Pulse width is limited by maximum junction temperature. Repetitive rating.

**Designer's Data for "Worst Case" Conditions** — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. SOA Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

Designer's is a trademark of Motorola, Inc.

Preferred devices are Motorola recommended choices for future use and best overall value.

REV 2



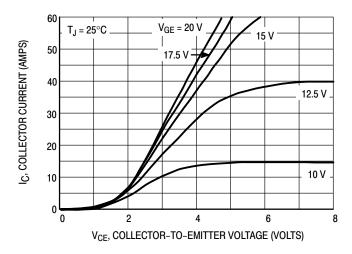
## MGW20N120

## **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = 25°C unless otherwise noted)

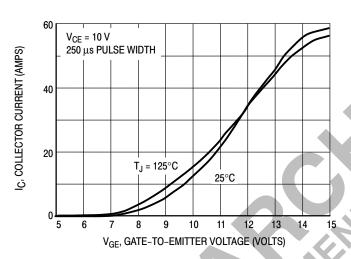
| Ch  | paracteristic  | Symbol               | Min         | Тур                  | Max         | Unit         |
|---|--|----------------------|-------------|----------------------|-------------|--------------|
| OFF CHARACTERISTICS   |  |                      |             |                      |             |              |
| Collector–to–Emitter Breakdown $(V_{GE} = 0 \text{ Vdc}, I_C = 25 \mu\text{Adc})$<br>Temperature Coefficient (Positi                                | · ·  | V <sub>(BR)CES</sub> | 1200<br>—   | —<br>870             | _           | Vdc<br>mV/°C |
| Emitter–to–Collector Breakdown Voltage (V <sub>GE</sub> = 0 Vdc, I <sub>EC</sub> = 100 mAdc)  |  | V <sub>(BR)ECS</sub> | 25          | _                    | _           | Vdc          |
| Zero Gate Voltage Collector Curre<br>(V <sub>CE</sub> = 1200 Vdc, V <sub>GE</sub> = 0 Vdc)<br>(V <sub>CE</sub> = 1200 Vdc, V <sub>GE</sub> = 0 Vdc, |  | ICES                 |             | _                    | 100<br>2500 | μAdc         |
| Gate-Body Leakage Current (V <sub>GI</sub>  | $= \pm 20 \text{ Vdc}, \text{ V}_{CE} = 0 \text{ Vdc})$                                | I <sub>GES</sub>     | _           | _                    | 250         | nAdc         |
| ON CHARACTERISTICS (1)  |  |                      |             |                      |             | _            |
|   | 9  | V <sub>CE(on)</sub>  | _<br>_<br>_ | 2.42<br>2.36<br>2.90 | 3.54        | Vdc          |
| Gate Threshold Voltage<br>(V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 1.0 mAdc)<br>Threshold Temperature Coeffic                          | ent (Negative)   | V <sub>GE(th)</sub>  | 4.0<br>—    | 6.0<br>10            | 8.0<br>—    | Vdc<br>mV/°C |
| Forward Transconductance (V <sub>CE</sub>   | = 10 Vdc, I <sub>C</sub> = 20 Adc)   | 9 <sub>fe</sub>      |             | 12                   | _           | Mhos         |
| DYNAMIC CHARACTERISTICS   |  |                      |             |                      |             |              |
| Input Capacitance   |  | C <sub>ies</sub>     | 7           | 1860                 | _           | pF           |
| Output Capacitance  | $(V_{CE} = 25 \text{ Vdc}, V_{GE} = 0 \text{ Vdc}, f = 1.0 \text{ MHz})$               | C <sub>oes</sub>     | _           | 122                  | _           |              |
| Transfer Capacitance  |  | C <sub>res</sub>     | _           | 29                   | _           |              |
| SWITCHING CHARACTERISTICS   | (1)  |                      |             |                      |             |              |
| Turn-On Delay Time  |  | t <sub>d(on)</sub>   | _           | 88                   | _           | ns           |
| Rise Time   | $(V_{CC} = 720 \text{ Vdc}, I_{C} = 20 \text{ Adc},$                                   | t <sub>r</sub>       | _           | 103                  | _           |              |
| Turn-Off Delay Time   | $V_{GE} = 15 \text{ Vdc}, L = 300 \mu H$<br>$R_{G} = 20 \Omega$                        | t <sub>d(off)</sub>  | _           | 190                  | _           |              |
| Fall Time   | Energy losses include "tail"   | t <sub>f</sub>       | _           | 284                  | _           |              |
| Turn-Off Switching Loss   |  | E <sub>off</sub>     | _           | 1.65                 | 2.75        | mJ           |
| Turn-On Delay Time  |  | t <sub>d(on)</sub>   | _           | 83                   | _           | ns           |
| Rise Time   | (V <sub>CC</sub> = 720 Vdc, I <sub>C</sub> = 20 Adc,                                   | t <sub>r</sub>       | _           | 107                  | _           |              |
| Turn-Off Delay Time   | $V_{GE} = 15 \text{ Vdc}, L = 300 \mu H$<br>$R_{G} = 20 \Omega, T_{J} = 125^{\circ}C)$ | t <sub>d(off)</sub>  | _           | 216                  | _           |              |
| Fall Time   | Energy losses include "tail"   | t <sub>f</sub>       | _           | 494                  | _           |              |
| Turn-Off Switching Loss   | 7,0  | E <sub>off</sub>     | _           | 3.19                 | _           | mJ           |
| Gate Charge   | 0  | Q <sub>T</sub>       | _           | 62                   | _           | nC           |
| 2   | $(V_{CC} = 720 \text{ Vdc}, I_{C} = 20 \text{ Adc}, V_{GF} = 15 \text{ Vdc})$          | Q <sub>1</sub>       | _           | 21                   | _           |              |
|   | v <sub>GE</sub> = 13 vuc)  | Q <sub>2</sub>       | _           | 25                   | _           |              |
| NTERNAL PACKAGE INDUCTAN  | CE   |                      |             |                      |             |              |
| Internal Emitter Inductance (Measured from the emitter lead   | d 0.25" from package to emitter bond pad)  | LE                   | _           | 13                   | _           | nH           |

<sup>(1)</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2%.

#### TYPICAL ELECTRICAL CHARACTERISTICS



**Figure 1. Output Characteristics** 



**Figure 3. Transfer Characteristics** 

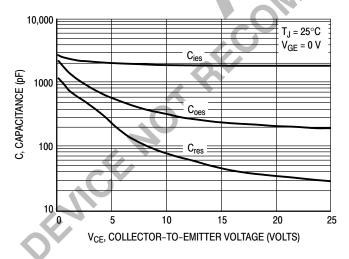


Figure 5. Capacitance Variation

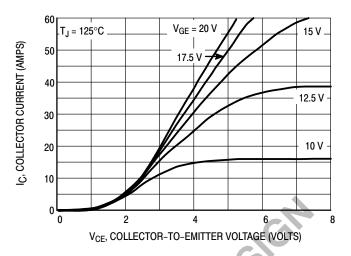


Figure 2. Output Characteristics

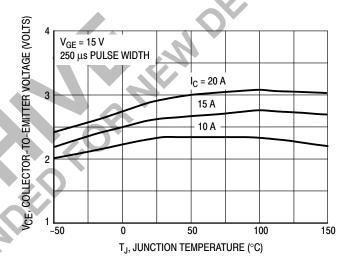


Figure 4. Collector-to-Emitter Saturation Voltage versus Junction Temperature

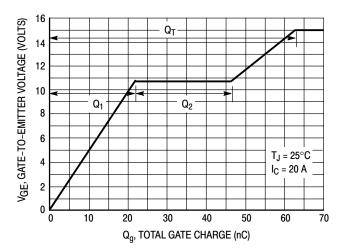


Figure 6. Gate-to-Emitter Voltage versus
Total Charge

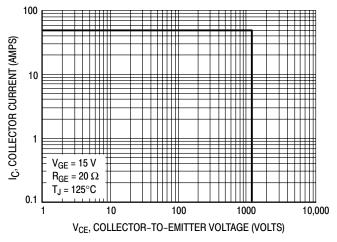


Figure 7. Reverse Biased Safe Operating Area

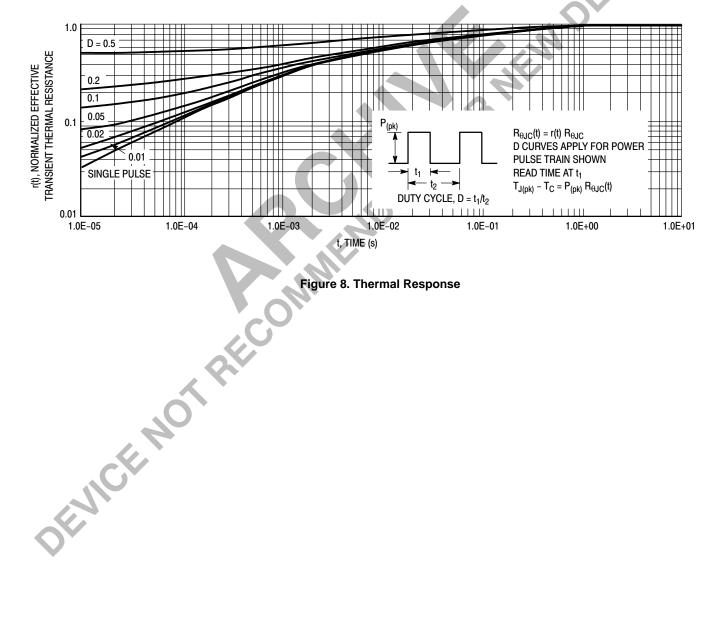
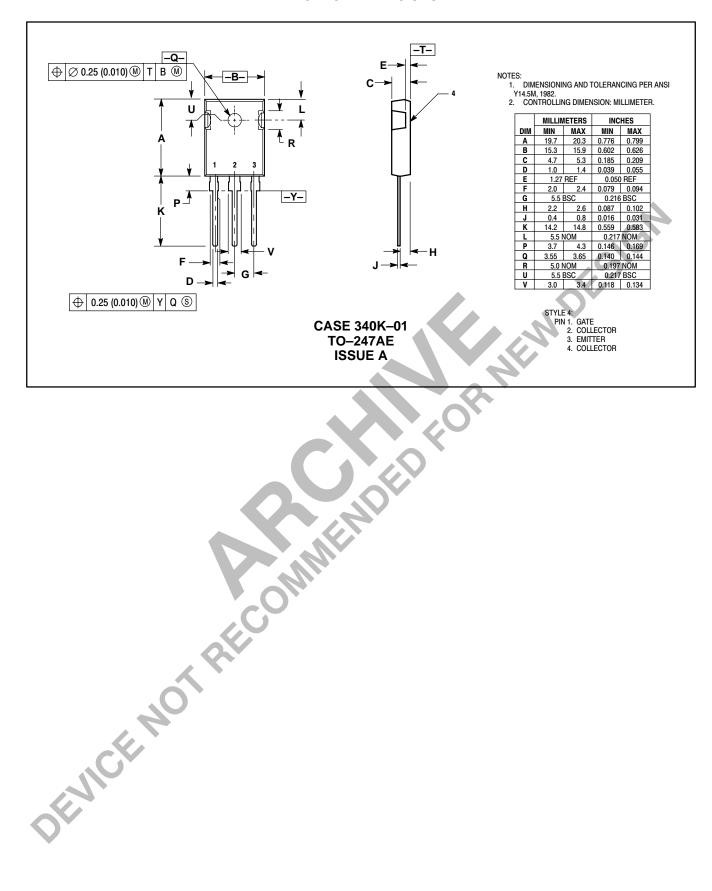


Figure 8. Thermal Response

#### PACKAGE DIMENSIONS





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